





ZHCSOD1K - DECEMBER 1982 - REVISED JUNE 2021



SN74HC14, SN54HC14

SNx4HC14 具有施密特触发输入的六路反相器

1 特性

缓冲输入

宽工作电压范围: 2V 至 6V

• 宽工作温度范围: -40°C 至 +85°C 支持多达 10 个 LSTTL 负载的扇出

与 LSTTL 逻辑 IC 相比,可显著降低功耗

2 应用

- 同步反相时钟输入
- 对开关进行去抖
- 对数字信号进行反相

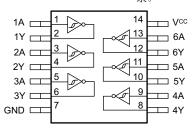
3 说明

此器件包含六个具有施密特触发输入的独立反相器。每 个逻辑门以正逻辑执行布尔函数 $Y = \overline{A}$ 。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
SN74HC14DR	SOIC (14)	8.70mm × 3.90mm
SN74HC14DBR	SSOP (14)	6.40 mm × 5.30 mm
SN74HC14NR	PDIP (14)	19.30mm × 6.40mm
SN74HC14NSR	SO (14)	10.20mm × 5.30mm
SN74HC14PWR	TSSOP (14)	5.00mm × 4.40mm
SN54HC14JR	CDIP (14)	21.30mm × 7.60mm
SN54HC14WR	CFP (14)	9.20mm × 6.29mm
SN54HC14FKR	LCCC (20)	8.90mm × 8.90mm

如需了解所有可用封装,请参阅数据表末尾的可订购产品附 录。



功能引脚分配

English Data Sheet: SCLS085



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	1 8.2 Functional Block Diagram

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Changes from Revision I (February 2016) to Revision J (October 2016)	Page
• 通篇将 "Y = A" 更改为 "Y = A"	1
• 向 <i>说明</i> 部分添加了 SNx4HC14	
• 删除了器件比较表部分	
Added Receiving Notification of Documentation Updates section	
Changes from Revision H (September 2015) to Revision I (February 2016)	Page
Changed part number from SN54HC08 to SN54HC14 in Switching Characteristics table	6
Changed part number from SN54HC08 to SN54HC14 in Switching Characteristics table	7

~ L	Shangaa from Basisian C (January 2014) to Basisian II (Contombas 2015)	Das
•	Changed part number from SN54HC08 to SN54HC14 in Switching Characteristics table	

_	nanges from Revision & (buildary 2014) to Revision if (beptember 2010)	· ug
•	添加了 <i>应用</i>	
•	向 <i>特性</i> 列表中添加了"军用免责声明"。	
•	添加了 <i>引脚配置和功能</i> 部分、ESD 等级 表、特性说明 部分、器件功能模式、应用和实施 部分、电源相	关建

Ch	nanges fro	om Revisio	n F (December 2010) to Revisi	on G (January 2014)	Page
	议部分、	布局部分、	器件和文档支持部分以及机械、	封装和可订购信息部分	1



5 Pin Configuration and Functions

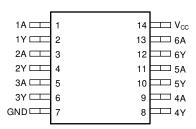


图 5-1. D, DB, N, NS, PW, J, or W Package 14-Pin SOIC, SSOP, PDIP, SO, TSSOP, CDIP, or CFP Top View

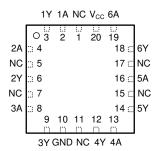


图 5-2. FK Package 20-Pin LCCC Top View

Pin Functions

PIN						
NAME	D, DB, N, NS, PW, J, or W	FK	I/O	DESCRIPTION		
1A	1	2	Input	Channel 1, Input A		
1Y	2	3	Output	Channel 1, Output Y		
2A	3	4	Input	Channel 2, Input A		
2Y	4	6	Output	Channel 2, Output Y		
3A	5	8	Input	Channel 3, Input A		
3Y	6	9	Output	Channel 3, Output Y		
GND	7	10	_	Ground		
4Y	8	12	Output	Channel 4, Output Y		
4A	9	13	Input	Channel 4, Input A		
5Y	10	14	Output	Channel 5, Output Y		
5A	11	16	Input	Channel 5, Input A		
6Y	12	18	Output	Channel 6, Output Y		
6A	13	19	Input	Channel 6, Input A		
V _{CC}	14	20	_	Positive Supply		
NC		1, 5, 7, 11, 15, 17	_	Not internally connected		



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		- 0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	Input clamp current ⁽²⁾ $V_I < 0$ or $V_I > V_{CC}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	V _O < 0		±20	mA
Io	Continuous output current	$V_{O} = 0$ to V_{CC}		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
TJ	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		- 60	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		2	5	6	V
VI	Input voltage		0		V _{CC}	V
Vo	Output voltage		0		V _{CC}	V
T _A	Operating free air temperature	SN54HC04	- 55		125	°C
	Operating free-air temperature SN74HC04		- 40		85	C

6.4 Thermal Information

		SN74HC14					
	THERMAL METRIC ⁽¹⁾	D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	UNIT
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
R ₀ JA	Junction-to-ambient thermal resistance	133.6	114.8	60.7	122.6	151.7	°C/W
R _θ JC(top)	Junction-to-case (top) thermal resistance	89	64.5	47.8	81.8	79.4	°C/W
R ₀ JB	Junction-to-board thermal resistance	89.5	65.1	40.6	83.8	94.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	45.5	23.7	26.9	45.4	25.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	89.1	64.4	40.3	83.4	94.1	°C/W

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				SN74HC14			
	THERMAL METRIC(1)	D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	UNIT
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
R _θ JC(bot)	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics - 74

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	Jordania in Columbia					perating	free-air	temperat	ure (T _A)		
P	ARAMETER	TES	T CONDITIONS	V _{cc}		25°C		-40°	C to 85°C	;	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
	Positive			2 V	0.7	1.2	1.5	0.7		1.5	
V _{T+}	switching			4.5 V	1.55	2.5	3.13	1.55		3.13	V
	threshold			6 V	2.1	3.3	4.2	2.1		4.2	
	Negative			2 V	0.3	0.6	1	0.3		1	
V _{T-}	switching			4.5 V	0.9	1.6	2.45	0.9		2.45	V
	threshold			6 V	1.2	2	3.2	1.2		3.2	
				2 V	0.2	0.6	1.2	0.2		1.2	
ΔV _T	Hysteresis (V _{T+} - V _{T-})			4.5 V	0.4	0.9	2.1	0.4		2.1	V
	(1-)			6 V	0.5	1.3	2.5	0.5		2.5	
				2 V	1.9	1.998		1.9			
			I _{OH} = -20 μA	4.5 V	4.4	4.499		4.4			
V _{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}		6 V	5.9	5.999		5.9			V
	output voltage	OI VIL	I _{OH} = -4 mA	4.5 V	3.98	4.3		3.84			
			I _{OH} = - 5.2 mA	6 V	5.48	5.8		5.34			
				2 V		0.002	0.1			0.1	
			I _{OL} = 20 μA	4.5 V		0.001	0.1			0.1	
V _{OL}	Low-level output voltage	V _I = V _{IH} or V _{IL}		6 V		0.001	0.1			0.1	V
	Tonago	0. V _{IL}	I _{OL} = 4 mA	4.5 V		0.17	0.26			0.33	
			I _{OL} = 5.2 mA	6 V		0.15	0.26			0.33	
I _I	Input leakage current	V _I = V _{CC} o	or 0	6 V			±0.1			±1	μA
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V			2			20	μA
C _i	Input capacitance			5 V		3	10			10	pF

6.6 Electrical Characteristics - 54

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

							Opera	ting free	air temp	peratur	e (T _A)			
ı	PARAMETER	TEST CO	NDITIONS	V _{cc}		25°C		- 40	°C to 85°	°C	- 55°	C to 125	5°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
	Positive switching threshold			2 V	0.7	1.2	1.5	0.7		1.5	0.7		1.5	
V _{T+}				4.5 V	1.55	2.5	3.13	1.55		3.13	1.55		3.13	V
				6 V	2.1	3.3	4.2	2.1		4.2	2.1		4.2	



over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

							Opera	ting free	air temp	eratur	e (T _A)			
ı	PARAMETER	TEST CO	NDITIONS	V _{cc}		25°C		- 40	°C to 85°	С	- 55°	C to 12	5°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
	Negative			2 V	0.3	0.6	1	0.3		1	0.3		1	
V _{T-}	switching			4.5 V	0.9	1.6	2.45	0.9		2.45	0.9		2.45	V
	threshold			6 V	1.2	2	3.2	1.2		3.2	1.2		3.2	
				2 V	0.2	0.6	1.2	0.2		1.2	0.2		1.2	
V_T	Hysteresis (V _{T+} - V _{T-})			4.5 V	0.4	0.9	2.1	0.4		2.1	0.4		2.1	V
	- 1-7			6 V	0.5	1.3	2.5	0.5		2.5	0.5		2.5	
				2 V	1.9	1.998		1.9			1.9			
			I _{OH} = -20 μA	4.5 V	4.4	4.499		4.4			4.4	·		
	High-level	V _I = V _{IH} or	'	6 V	5.9	5.999		5.9			5.9			
V _{OH}	output voltage	V _{IL}	I _{OH} = -4 mA	4.5 V	3.98	4.3		3.84			3.7			V
			I _{OH} = - 5.2 mA	6 V	5.48	5.8		5.34			5.2			
				2 V		0.002	0.1			0.1			0.1	
			I _{OL} = 20 μΑ	4.5 V		0.001	0.1			0.1			0.1	
V _{OL}	Low-level output	$V_I = V_{IH}$ or		6 V		0.001	0.1			0.1			0.1	V
	voltage	V _{IL}	I_{OL} = 4 mA	4.5 V		0.17	0.26			0.33			0.33	
			I _{OL} = 5.2 mA	6 V		0.15	0.26			0.33			0.33	
I _I	Input leakage current	V _I = V _{CC} or		6 V			±0.1			±1			±1	μΑ
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V			2			20			40	μΑ
Ci	Input capacitance			2 V to 6 V		3	10			10			10	pF

6.7 Switching Characteristics - 74

over operating free-air temperature range (unless otherwise noted)

					Op	erating	free-air	tempera	ture (T _A)		
	PARAMETER	FROM	то	V _{cc}		25°C		- 40)°C to 85	°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
				2 V		55	125			155	
t _{pd}	Propagation delay	A	Υ	4.5 V		12	25			31	ns
				6 V		11	21			26	
				2 V		38	75			95	
t _t	Transition-time		Υ	4.5 V		8	15			19	ns
				6 V		6	13			16	



6.8 Switching Characteristics - 54

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

	-					(Operati	ng free	air ten	nperatu	ıre (T _A)			
	PARAMETER	FROM	то	V _{CC}		25°C		- 40	°C to 8	5°C	- 55°	C to 12	25°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
				2 V		55	125			155			190	
t _{pd}	Propagation delay	Α	Υ	4.5 V		12	25			31	38			ns
				6 V		11	21			26			22	
				2 V		38	75			95			110	
t _t	Transition-time	Y 4.5 V 8 15 19				22	ns							
				6 V		6	13		16			19		

6.9 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	UNIT
C _{pd} Power dissipation capa per gate	no load	2 V to 6 V		20		pF

6.10 Typical Characteristics

 $T_A = 25^{\circ}C$

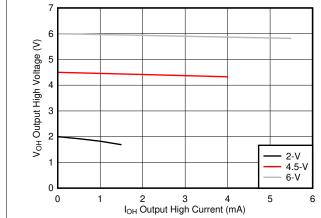


图 6-1. Typical output voltage in the high state (V_{OH})

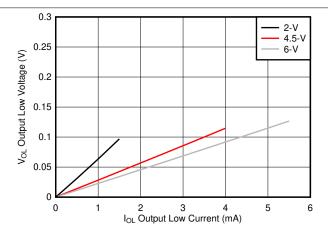
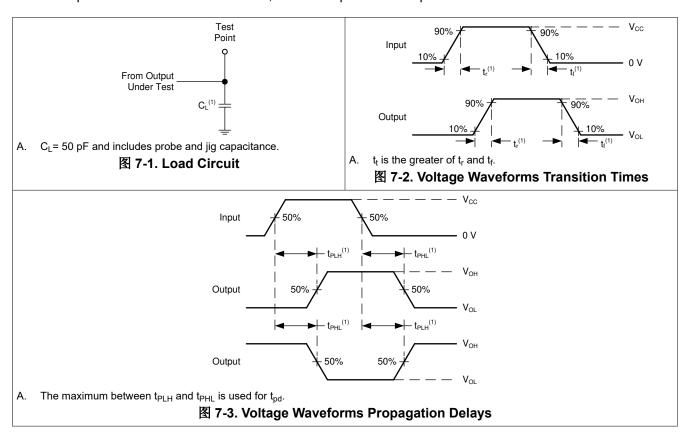


图 6-2. Typical output voltage in the low state (V_{OL})



7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 6 ns.
- The outputs are measured one at a time, with one input transition per measurement.

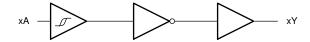


8 Detailed Description

8.1 Overview

This device contains six independent inverters with Schmitt-trigger inputs. Each gate performs the Boolean function $Y = \overline{A}$ in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

The SN74HC14 can drive a load with a total capacitance less than or equal to the maximum load listed in the Switching Characteristics - 74 connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the Absolute Maximum Ratings.

8.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the *Electrical Characteristics - 74*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics - 74*, using ohm's law $(R = V \div I)$.

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Cahracteristics* -74, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs slowly will also increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

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8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in 🗵 8-1.

CAUTION

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

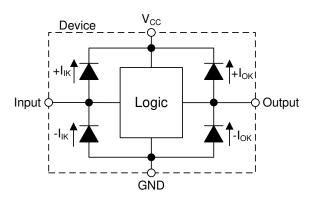


图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table

INPUT	OUTPUT
Α	Y
L	Н
Н	L

9 Application and Implementation

备注

以下应用部分的信息不属于 TI 组件规范, TI 不担保其准确性和完整性。客户应负责确定 TI 组件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

9.1 Application Information

This device can be used to add an additional stage to a counter with an external flip-flop. Because counters use a negative edge trigger, the flip-flop's clock input must be inverted to provide this function. This function only requires one of the six available inverters in the device, so the remaining channels can be used for other applications needing an inverted signal or improved signal integrity. Unused inputs must be terminated at V_{CC} or GND. Unused outputs can be left floating.

9.2 Typical Application

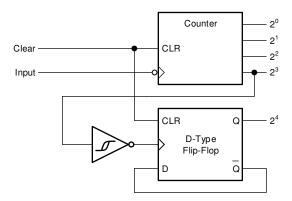


图 9-1. Typical application schematic

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics - 74*.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HC14 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics - 74*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the *Absolute Maximum Ratings*.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, T_J(max) listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-}(min)$ to be considered a logic LOW, and $V_{t+}(max)$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC14, as specified in the *Electrical Characteristics - 74*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HC14 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the ΔV_T (min) in the *Electrical Characteristics - 74*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the Feature Description for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics - 74*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics 74*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Feature Description for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the
 device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the Layout.
- 2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC14 to the receiving device.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_O(max)) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

9.2.3 Application Curves

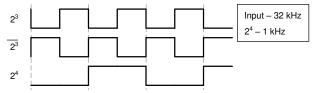


图 9-2. Typical application timing diagram



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in 811-1.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

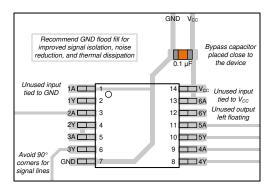


图 11-1. Example layout for the SN74HC14



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- · Designing with Logic

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.3 Trademarks

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12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8409101VCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8409101VC A SNV54HC14J	Samples
5962-8409101VDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8409101VD A SNV54HC14W	Samples
84091012A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84091012A SNJ54HC 14FK	Samples
8409101CA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8409101CA SNJ54HC14J	Samples
8409101DA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8409101DA SNJ54HC14W	Samples
JM38510/65702BCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65702BCA	Samples
JM38510/65702BDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65702BDA	Samples
M38510/65702BCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65702BCA	Samples
M38510/65702BDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65702BDA	Samples
SN54HC14J	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	SN54HC14J	Samples
SN74HC14DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14DRG3	ACTIVE	SOIC	D	14	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC14N	Samples
SN74HC14NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC14N	Samples

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Orderable Device	Status	Package Type	Package Drawing	ckage Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Sample
						(6)				

Orderable Device	(1)	Раскаде туре	Drawing Drawing	Pins	Qty	(2)	Ball material	(3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC14NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14NSRE4	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SN74HC14PWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC14	Samples
SNJ54HC14FK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84091012A SNJ54HC 14FK	Samples
SNJ54HC14J	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8409101CA SNJ54HC14J	Samples
SNJ54HC14W	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8409101DA SNJ54HC14W	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54HC14, SN54HC14-SP, SN74HC14:

Catalog: SN74HC14, SN54HC14

Automotive: SN74HC14-Q1, SN74HC14-Q1

Military: SN54HC14

• Space : SN54HC14-SP

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military QML certified for Military and Defense Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application



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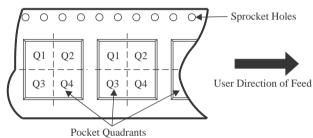
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

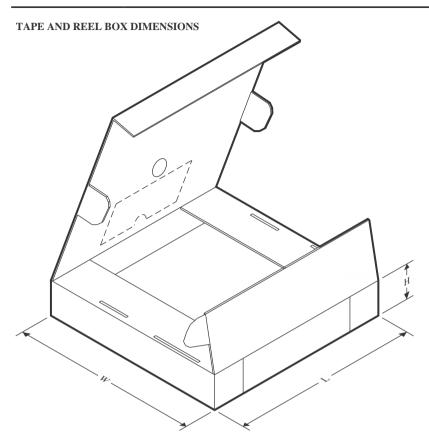


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC14DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74HC14DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC14DRG3	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HC14DRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC14NSR	so	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1
SN74HC14NSR	so	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1
SN74HC14PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HC14PWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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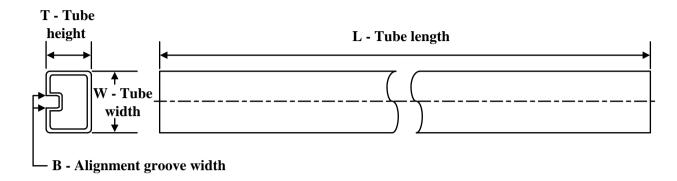
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC14DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74HC14DR	SOIC	D	14	2500	367.0	367.0	38.0
SN74HC14DRG3	SOIC	D	14	2500	366.0	364.0	50.0
SN74HC14DRG4	SOIC	D	14	2500	356.0	356.0	35.0
SN74HC14NSR	so	NS	14	2000	367.0	367.0	38.0
SN74HC14NSR	so	NS	14	2000	356.0	356.0	35.0
SN74HC14PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74HC14PWRG4	TSSOP	PW	14	2000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-8409101VDA	W	CFP	14	25	506.98	26.16	6220	NA
84091012A	FK	LCCC	20	55	506.98	12.06	2030	NA
8409101DA	W	CFP	14	25	506.98	26.16	6220	NA
JM38510/65702BDA	W	CFP	14	25	506.98	26.16	6220	NA
M38510/65702BDA	W	CFP	14	25	506.98	26.16	6220	NA
SN74HC14N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC14N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC14NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC14NE4	N	PDIP	14	25	506	13.97	11230	4.32
SNJ54HC14FK	FK	LCCC	20	55	506.98	12.06	2030	NA
SNJ54HC14W	W	CFP	14	25	506.98	26.16	6220	NA

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE

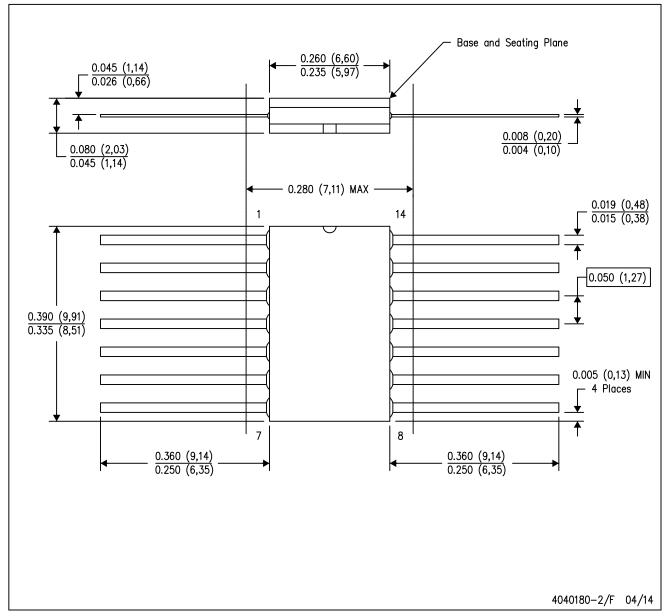


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14



8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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